

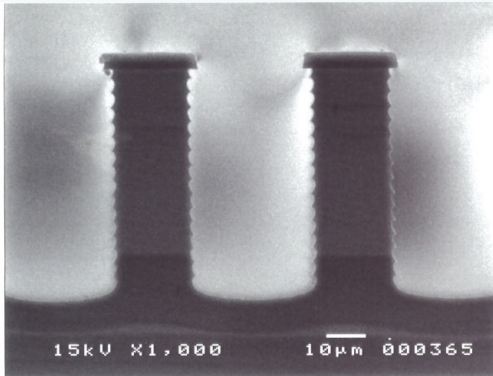
High Density Plasma

High-speed Silicon Deep Etching System Designed Specifically for R&D

MODEL RIE-400iPB

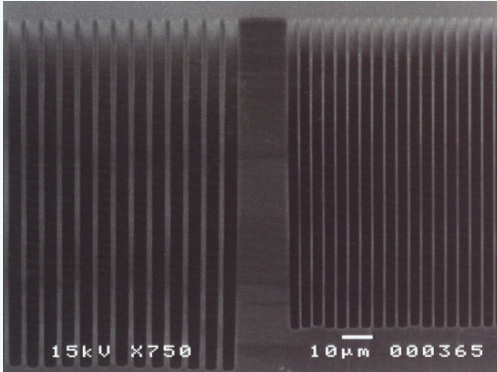
Examples of Etching Process

—High Rate Etching—



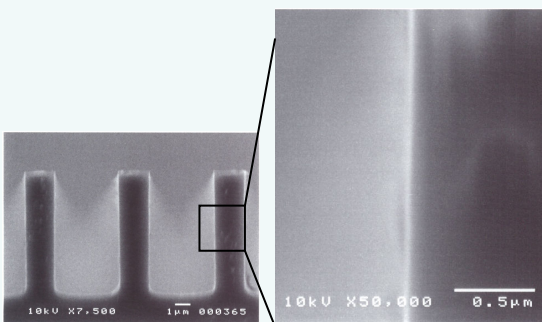
Etch Rate: 14 μ m/min

—High Aspect Etching—



Etch Rate: 3 μ m/min
Aspect Ratio: 31
Etch Depth: 95 μ m

—Low Scalloping—



Pattern Width: 4 μ m
Etch Depth: 8 μ m



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The SAMCO RIE-400iPB is an inductively coupled plasma RIE system that uses high-density plasma to perform **high speed silicon etching** required in the fabrication of MEMS and electronic devices.

The system, capable of etching **up to 4" wafers**, was designed to provide all the high-performance features of the larger RIE-800iPB in an **easy to use**, easy to maintain, **affordable package**.

An optional SiO₂ etching kit offers the ability to perform precise, highly **controllable SiO₂ etching** with minimum changeover time. By allowing users to process both SiO₂ and Si the system provides **Maximum Value to Customers!**

Features

- **High Speed, Highly Selective, Deep Si Etching** is made possible using an unique plasma source and chamber specifically designed for the "Bosch Process".
- **Specifically Designed for R&D** - easy to use, easy to maintain, high cost-performance package!
- **SiO₂ Etching Kit** available as an option
- **High Rate Etching** – greater than 14 μm/min
- **Low Scalloping** through high speed gas switching
- **Through Wafer** etching (depth: 600 μm)
- **SOI** (silicon on insulator) notch prevention technology

Specification

Reaction Chamber	Al, inner diameter φ 320mm
Substrate Stage	Al, φ 106mm
Load lock Chamber	Al, outer measurement 340(W) × 445(D) × 144(H)mm
ICP RF Power	13.56MH, crystal oscillation, Max.1kW, automatching
BIAS RF Power	13.56MHz, crystal oscillation, Max.300W, automatching
Gas Lines	4 mass flow controlled lines (<i>optional lines available</i>)
Vacuum Gauges	R. Chamber : diaphragm gauge 1 (1.33 × 10 ⁻² ~1.33 × 10 ⁻² Pa) L.L Chamber: crystal gauge (atmospheric~1 × 10 ⁻² Pa)
Vacuum System	R. Chamber : turbo molecular pump (1300L/sec) + dry pump (1300L/min) L.L Chamber: dry pump (shares R.C. pump)
Operation Method	Touch panel operation with recipe management
Dimensions	986(W) × 1790(D) × 1975(H)mm

Applications

- Fabrication of acceleration sensors, gyro sensors, actuators etc
- Inkjet printer head
- Through Silicon Via (TSV) for 3D packaging
- Manufacturing of medical devices (μTAS, etc)

Options

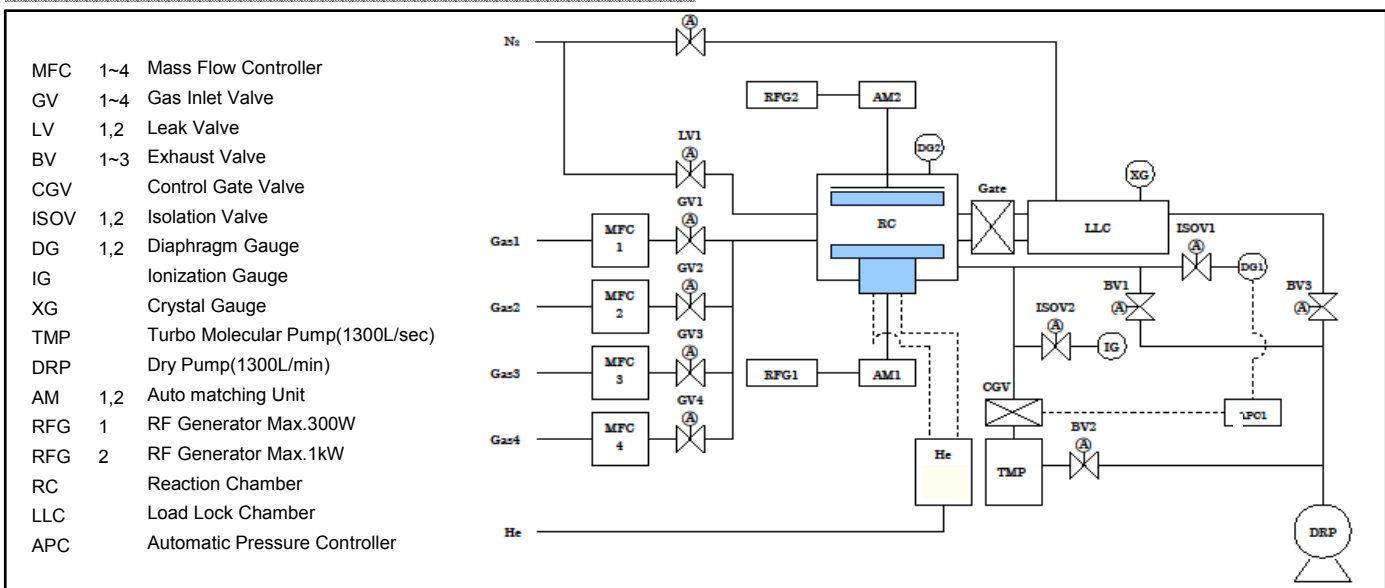
- Circulator (For TMP and Dry pump cooling)
- SiO₂ etching Kit

▲Please contact SAMCO for details regarding other options

Utilities

Power Supply	AC200V, 3 φ 75A
Earth	Type D ground
Cooling	System Over 2L/min
	DRP 4~8L/min
Evacuation Duct	Main body
	Gas box
	Dry pump
Compressed Air	0.5~0.7MPa(G)
N ₂	System 0.1MPa(G)
	DRP 0.1~0.7MPa(G)
Exhaust Ducts	For dry pump

Flow Sheet



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